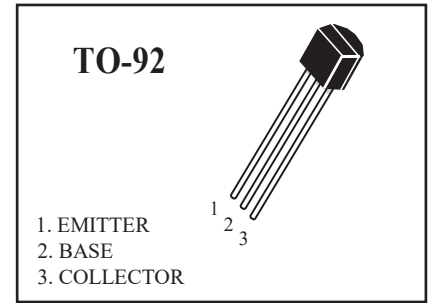
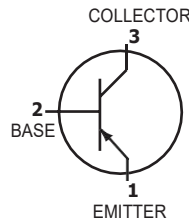




Plastic-Encapsulate Transistors

PNP Silicon

Lead(Pb)-Free



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Rating	Symbol	SS8550	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V <sub>dc</sub>
Collector-Base Voltage	V <sub>CBO</sub>	-40	V <sub>dc</sub>
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V <sub>dc</sub>
Collector Current	I <sub>C</sub>	-1.5	A <sub>dc</sub>
Total Device Dissipation T <sub>A</sub> =25°C	P <sub>D</sub>	1.0	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

DEVICE MARKING

SS8550=SS8550D
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ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = -0.1 mA <sub>dc</sub> , I <sub>B</sub> =0)	V <sub>(BR)CEO</sub>	-25	-	V <sub>dc</sub>
Collector-Base Breakdown Voltage (I <sub>C</sub> = -100 uA <sub>dc</sub> , I <sub>E</sub> =0)	V <sub>(BR)CBO</sub>	-40	-	V <sub>dc</sub>
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -100 uA <sub>dc</sub> , I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	-5.0	-	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = -40 V <sub>dc</sub> , I <sub>E</sub> =0 V <sub>dc</sub> )	I <sub>CBO</sub>	-	-0.1	uA <sub>dc</sub>
Emitter Cutoff Current(V <sub>EB</sub> = -5 V <sub>dc</sub> , I <sub>C</sub> =0 V <sub>dc</sub> )	I <sub>EBO</sub>	-	-0.1	uA <sub>dc</sub>

1. Pulse Test: Pulse Width ≤ 300 us, Duty Cycle ≤2.0%



**ELECTRICAL CHARACTERISTICS**( $T_A=25$  unless otherwise noted) (Continued)

Characteristics	Symbol	Min	TYP	Max	Unit
DC Current Gain ( $I_C = -100$ mAdc, $V_{CE} = -1.0$ Vdc)	$h_{FE(1)}$	85	-	400	-
DC Current Gain ( $I_C = -800$ mAdc, $V_{CE} = -1.0$ Vdc)	$h_{FE(2)}$	40	-	-	-
Collector-Emitter Saturation Voltage ( $I_C = -800$ mAdc, $I_B = -80$ mAdc)	$V_{CE(sat)}$	-	-	-0.5	Vdc
Base-Emitter Saturation Voltage ( $I_C = -800$ mAdc, $I_B = -80$ mAdc)	$V_{BE(sat)}$	-	-	-1.2	Vdc
Transition Frequency ( $V_{CE} = -10$ V, $I_C = -50$ mA, $f = 30$ MHz)	$f_T$	100	-	-	MHz

**Classification of  $h_{FE(1)}$**

Rank	B	C	D	E
Range	85-160	120-200	160-300	300-400

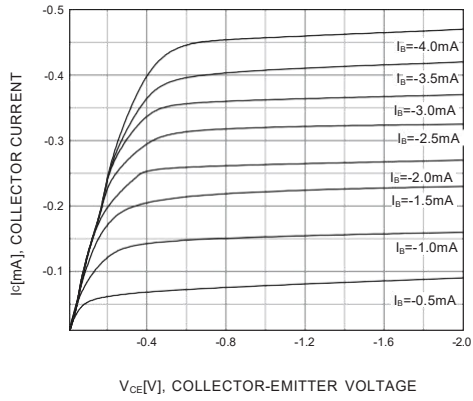


FIG.1 Static Characteristic

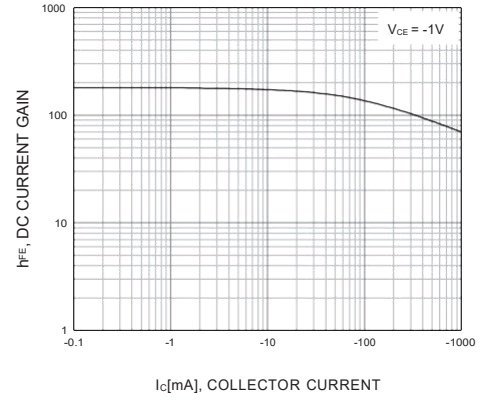


FIG.2 DC Current Gain

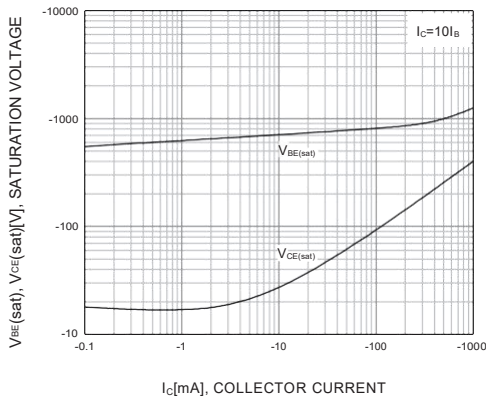


FIG.3 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

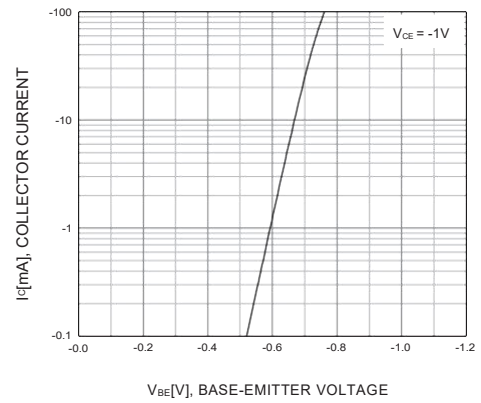


FIG.4 Base-Emitter On Voltage

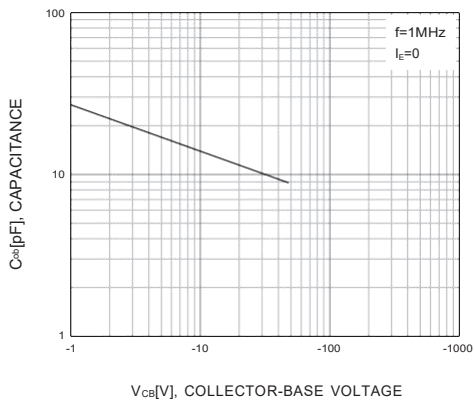


FIG.5 Collector Output Capacitance

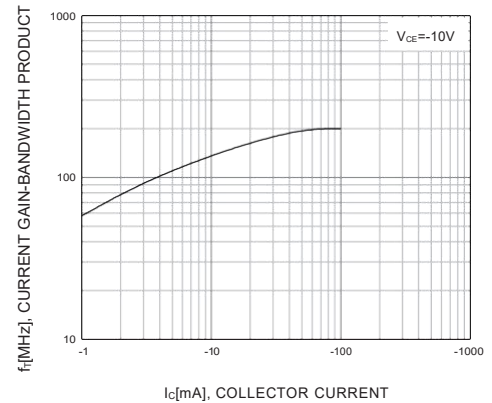
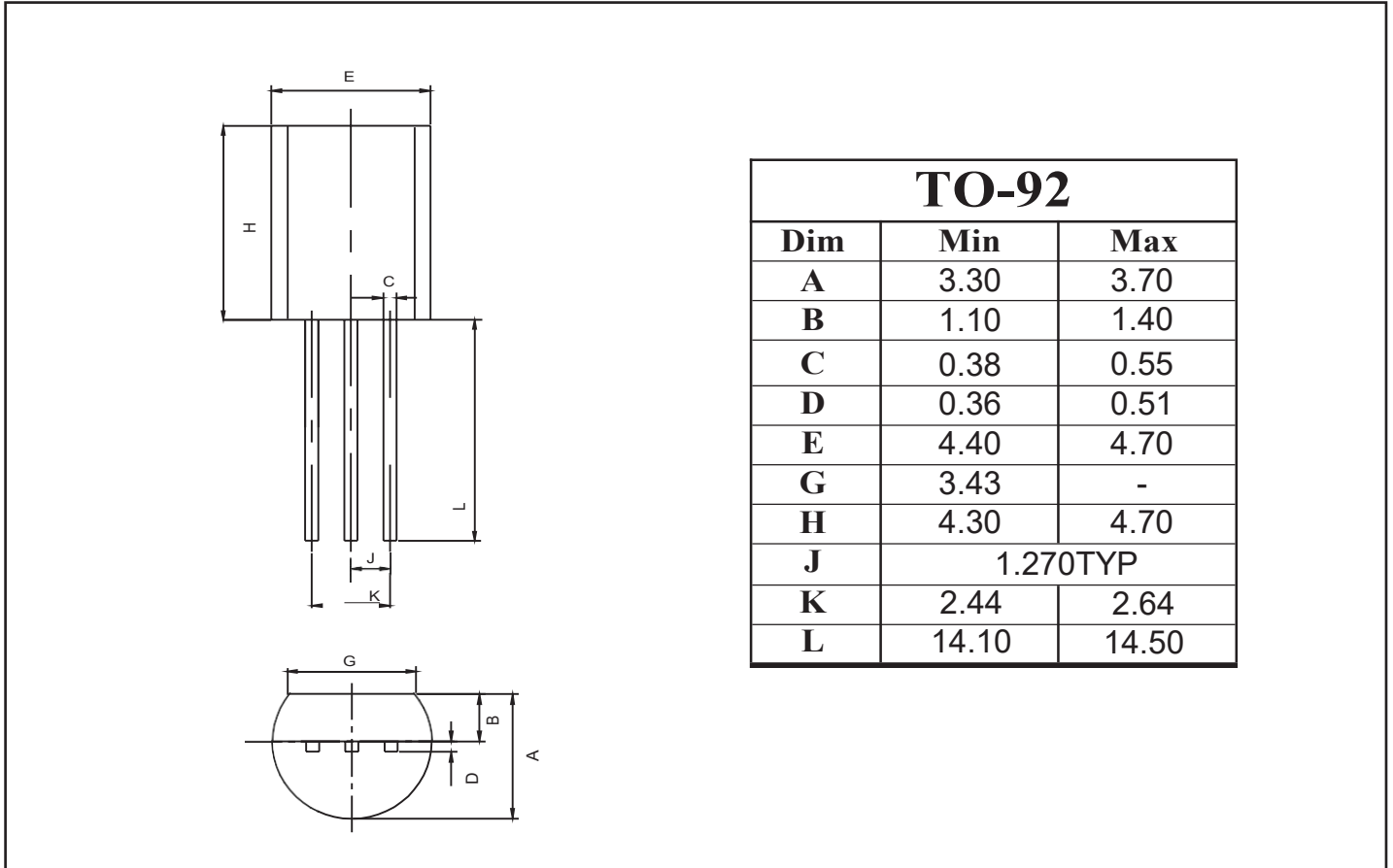


FIG.6 Current Gain Bandwidth Product



### TO-92 Outline Dimensions

unit:mm



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